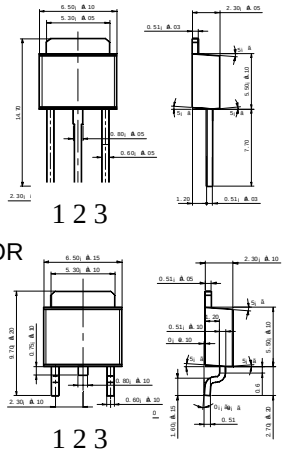
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-251/252 Plastic-Encapsulate Transistors

D882 TRANSISTOR (NPN)

TO-251
TO-252-2



1. BASE
2. COLLECTOR
3. EMITTER

FEATURES

Power dissipation

P_{CM}: 1.25 W (Tamb=25℃)

Collector current

I_{CM}: 3 A

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= 100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic= 10 mA, I_B=0	30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA, I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}= 40V, I_E=0			1	μA
Collector cut-off current	I_{CEO}	V_{CE}= 30V, I_B=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 6V, I_C=0			1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= 2V, IC= 1A	60		400	
	$h_{FE(2)}$	V_{CE}= 2V, I_C= 100mA	32			
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C= 2A, I_B= 0.2 A			0.5	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C= 2A, I_B= 0.2 A			1.5	V
Transition frequency	f_T	V_{CE}= 5V, Ic=0.1A f =10MHz	50			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400